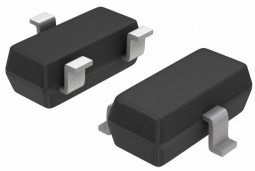
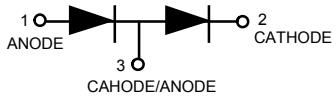
Dual Series Switching Diode

BAV99LT1G
SBAV99LT1G

- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SOT–23



DEVICE MARKING ORDERING INFORMATION

Device	Marking	Shipping
BAV99LT1G SBAV99LT1G	A7	3000 Tape & Reel
BAV99LT3G SBAV99LT3G	A7	10000 Tape & Reel

MAXIMUM RATINGS (EACH DIODE)

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	70	Vdc
Forward Current	I_F	215	mAdc
Peak Forward Surge Current	$I_{FM(surge)}$	500	mAdc
Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Average Rectified Forward Current (1) (averaged over any 20 ms period)	$I_{F(AV)}$	715	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non–Repetitive Peak Forward Current	I_{FSM}		A
t = 1.0 μ s		2.0	
t = 1.0 ms		1.0	
t = 1.0 S		0.5	

THERMAL CHARACTERISTICS

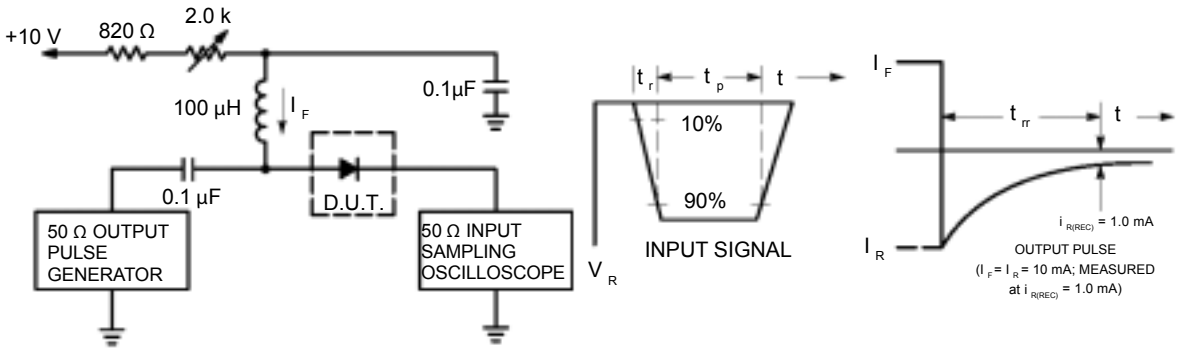
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board, (1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	–65 to +150	°C

1. FR–5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

BAV99LT1G , SBAV99LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage($I_{(BR)}$ = 100 µA)	$V_{(BR)}$	70	—	Vdc
Reverse Voltage Leakage Current (V_R = 70 Vdc)	I_R	—	2.5	µAdc
(V_R = 25 Vdc, T_J = 150°C)		—	30	
(V_R = 70 Vdc, T_J = 150°C)		—	50	
Diode Capacitance (V_R = 0, f = 1.0 MHz)	C_D	—	1.5	pF
Forward Voltage (I_F = 1.0 mAdc)	V_F	—	715	mVdc
(I_F = 10 mAdc)		—	855	
(I_F = 50 mAdc)		—	1000	
(I_F = 150 mAdc)		—	1250	
Reverse Recovery Time (I_F = I_R = 10 mAdc, $i_{R(REC)}$ = 1 0 mAdc, R_L = 100Ω) (Figure 1)	t_{rr}	—	6.0	ns
Forward Recovery Voltage (I_F = 10 mA, t_r = 20 ns)	V_{FR}	—	1.75	V



Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

CURVES APPLICABLE TO EACH DIODE

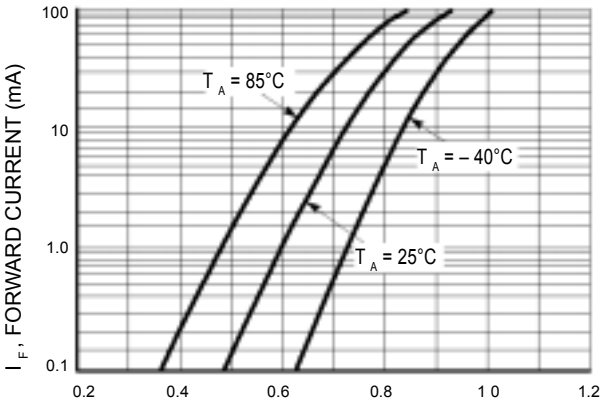


Figure 2. Forward Voltage

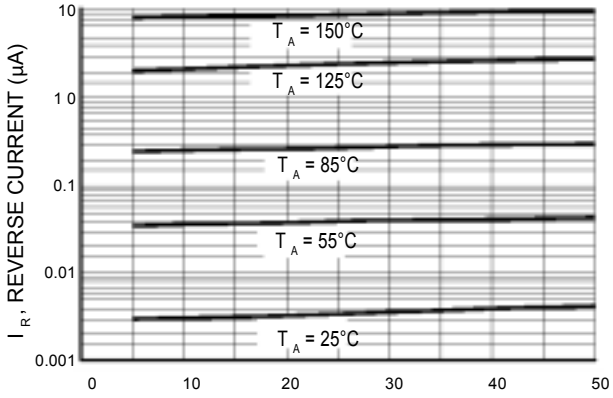


Figure 3. Leakage Current

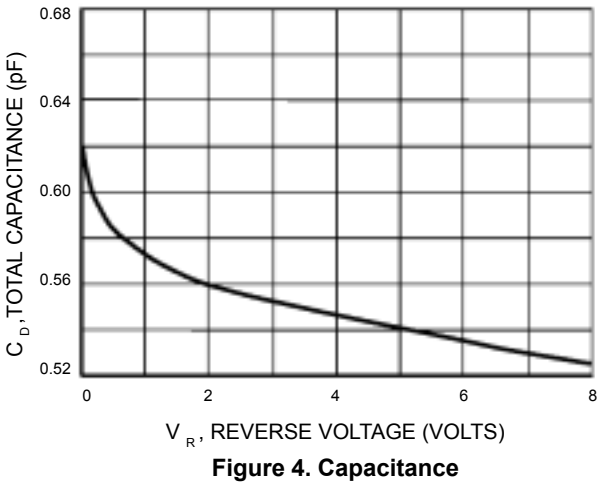
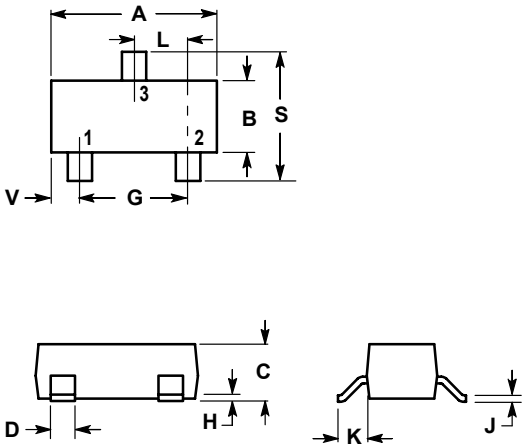


Figure 4. Capacitance

BAV99LT1G , SBAV99LT1G

SOT-23

Dimension Outline:



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

P N 1. ANODE
2. CAHODE
3. CAHODE/ANODE

Soldering Footprint: